

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.34	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.1	2.7	V	$I_C = 12A, V_{GE} = 15V$
		—	2.45	—		$I_C = 23A, V_{GE} = 15V$
		—	1.95	—		$I_C = 12A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	11	16	—	S	$V_{CE} = 100V, I_C = 12A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	51	76	nC	$I_C = 12A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	7.6	11		$V_{CC} = 400V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	18	27		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	25	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 12A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$
t_r	Rise Time	—	16	—		
$t_{d(off)}$	Turn-Off Delay Time	—	99	150		
t_f	Fall Time	—	67	100		
E_{on}	Turn-On Switching Loss	—	0.13	—	mJ	Energy losses include "tail" See Fig. 10, 11, 13, 14
E_{off}	Turn-Off Switching Loss	—	0.13	—		
E_{ts}	Total Switching Loss	—	0.26	0.35		
$t_{d(on)}$	Turn-On Delay Time	—	24	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 12A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$
t_r	Rise Time	—	17	—		
$t_{d(off)}$	Turn-Off Delay Time	—	150	—		
t_f	Fall Time	—	150	—		
E_{ts}	Total Switching Loss	—	0.55	—	mJ	See Fig. 13, 14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	980	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	71	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	18	—		$f = 1.0MHz$

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu H$, $R_G = 23\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

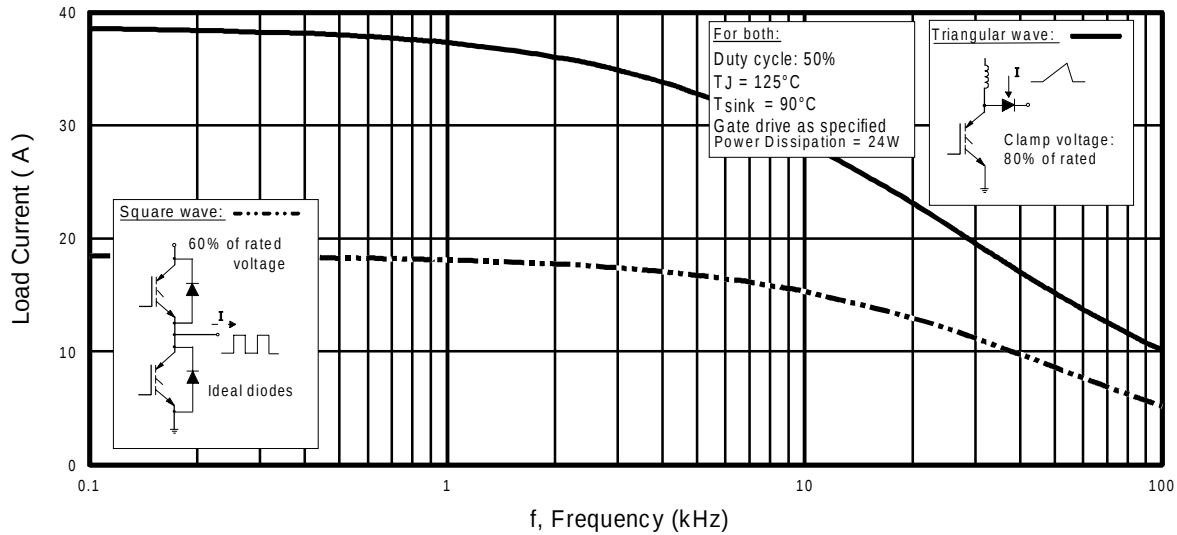


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{\text{RMS}}$ of fundamental; for triangular wave, $I = I_{\text{PK}}$)

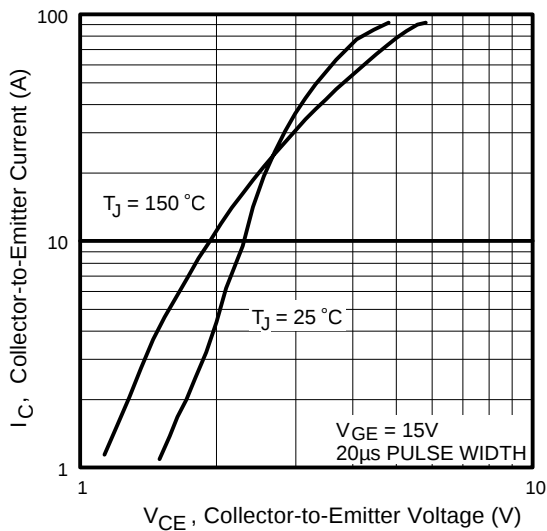


Fig. 2 - Typical Output Characteristics

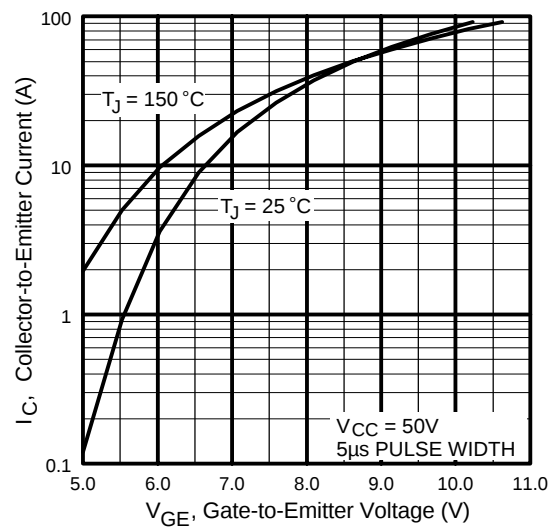


Fig. 3 - Typical Transfer Characteristics

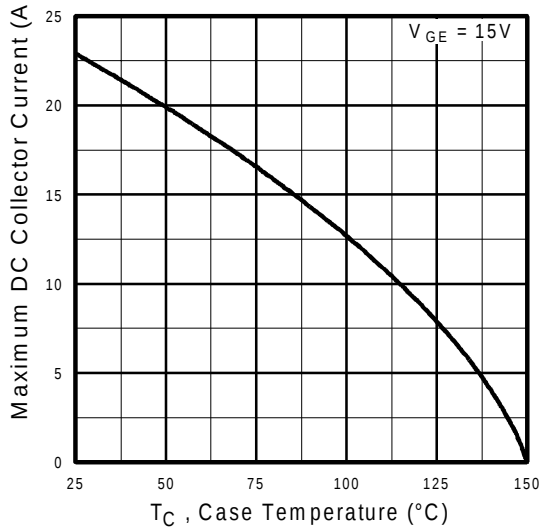


Fig. 4 - Maximum Collector Current vs. Case Temperature

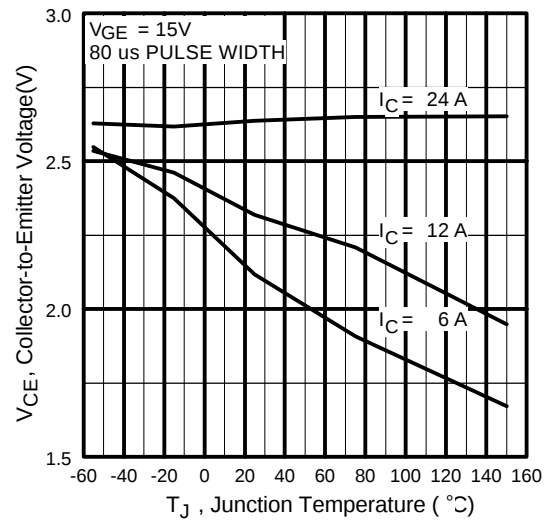


Fig. 5 - Collector-to-Emitter Voltage vs. Junction Temperature

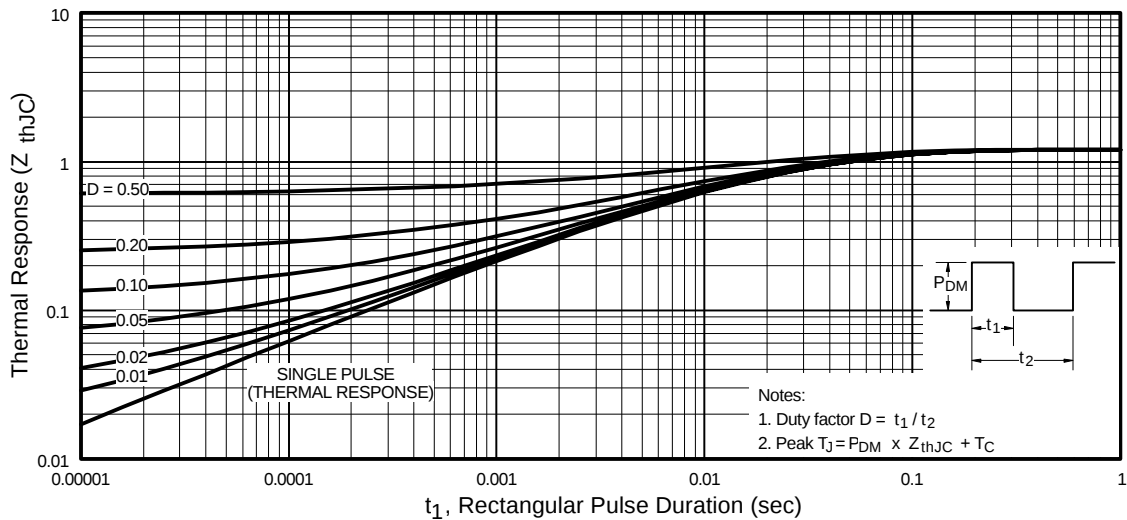


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

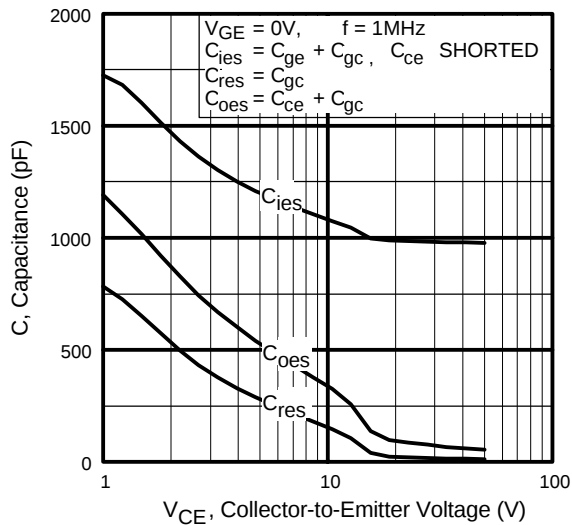


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

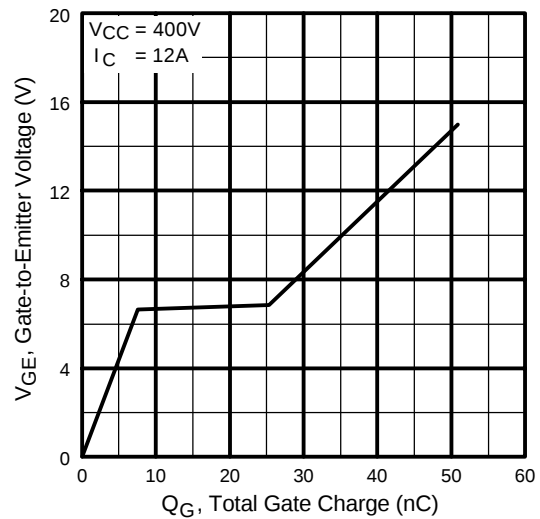


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

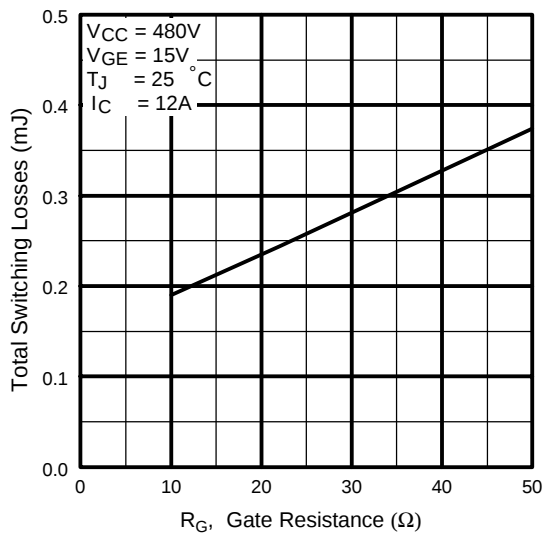


Fig. 9 - Typical Switching Losses vs. Gate Resistance

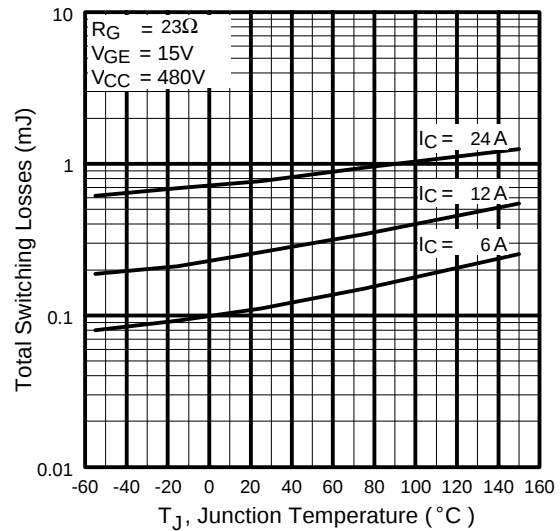


Fig. 10 - Typical Switching Losses vs. Junction Temperature

IRG4PC30W

International
IR Rectifier

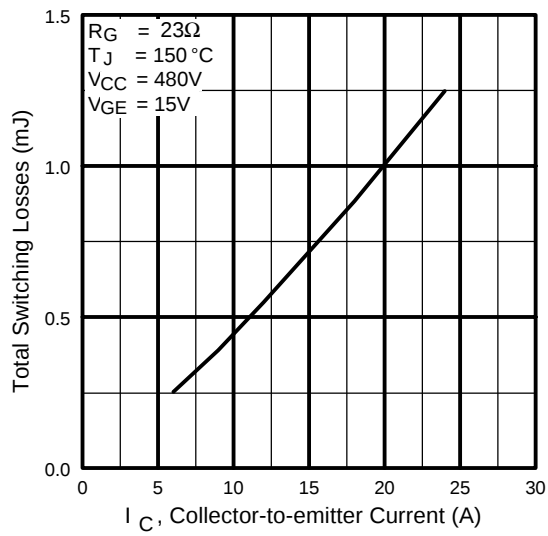


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

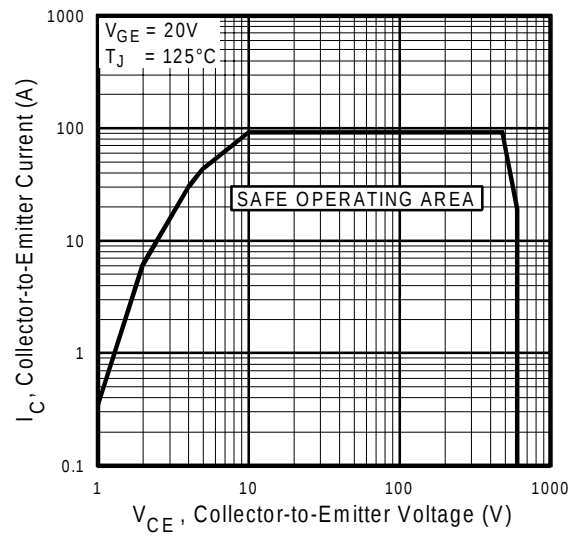


Fig. 12 - Turn-Off SOA

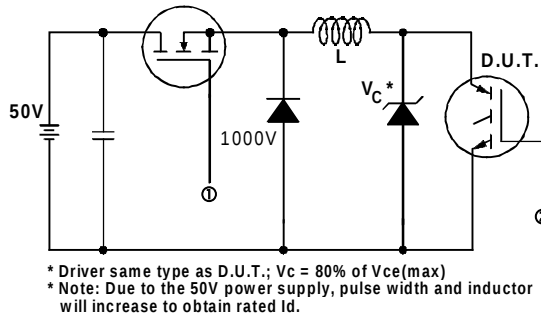


Fig. 13a - Clamped Inductive Load Test Circuit

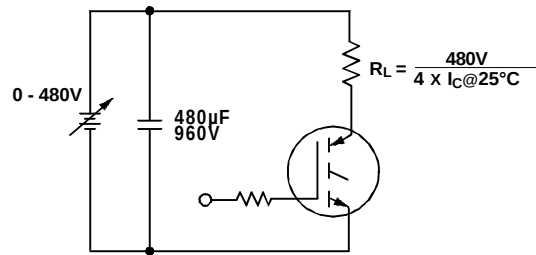


Fig. 13b - Pulsed Collector Current Test Circuit

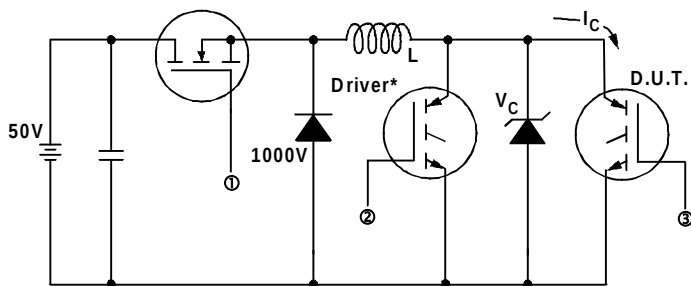


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 480V$

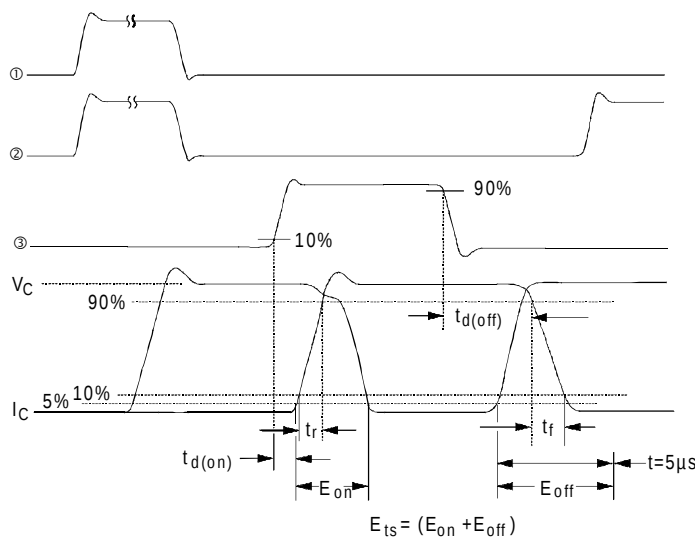
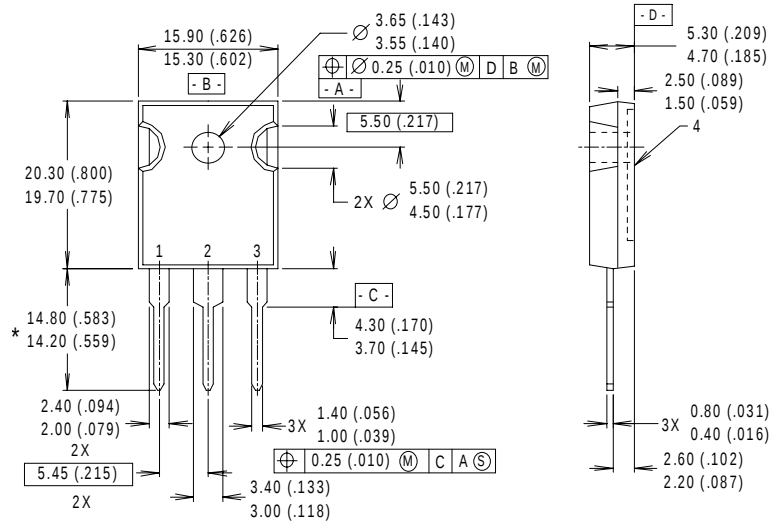


Fig. 14b - Switching Loss Waveforms

IRG4PC30W

International
IR Rectifier

Case Outline and Dimensions — TO-247AC



NOTES:

- 1 DIMENSIONS & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH.
- 3 DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
- 4 CONFORMS TO JEDEC OUTLINE TO-247AC.

LEAD ASSIGNMENTS

- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER
- 4 - COLLECTOR

* LONGER LEADED (20mm)
VERSION AVAILABLE (TO-247AD)
TO ORDER ADD "-E" SUFFIX
TO PART NUMBER

CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)

Dimensions in Millimeters and (Inches)

International
IR Rectifier

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IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
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Data and specifications subject to change without notice. 4/00

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>